			DB	Time stamp
Number	Hits	Search Text	USPAT;	2002/10/21 12:56
- Williams	455704	diode	US-PGPUB;	
	ļ		EPO; JPO;	
	ļ		DERWENT	
	ŧ		USPAT;	2002/10/21 12:56
-	23957	Schottky	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
			USPAT;	2002/10/21 12:57
-	58252	MOS adj transistor	US-PGPUB;	
	30202	•	EPO; JPO;	
			DERWENT	1
			USPAT;	2002/10/21 12:57
-	1.53048	silicon near5 substrate	US-PGPUB;	
	133040		EPO; JPO;	
			DERWENT	
			USPAT;	2002/10/21 12:59
-	45236	silicide	US-PGPUB;	2002, 2-1
	45250	31110100	EPO; JPO;	
			DERWENT	2002/10/21 13:01
-	156	diode and Schottky and (MOS adj	USPAT;	2002/10/22 ===
	156	transistor) and (silicon near5 substrate)	US-PGPUB;	
		and silicide	EPO; JPO;	
			DERWENT	2002/10/21 13:0
-		(titanium tungsten cobalt platinum) near5	USPAT;	2002/10/21 13:0
	3	(titanium tungstem communi	US-PGPUB;	
		silicode	EPO; JPO;	
			DERWENT	2002/10/21 13:0
	1	(titanium tungsten cobalt platinum) near5	USPAT;	2002/10/21 13:0
	17605	(titanium tungsten cobare para	US-PGPUB;	
		silicide	EPO; JPO;	
			DERWENT	
		, a lather and (MOS add	USPAT;	2002/10/21 13:0
-	98	diode and Schottky and (MOS adj transistor) and (silicon near5 substrate)	US-PGPUB;	1
		transistor) and (SIIIcon hears shalt platinum)	EPO; JPO;	
		and ((titanium tungsten cobalt platinum)	DERWENT	101 101 10
		near5 silicide)	USPAT;	2002/10/21 13:0
	1 3	nears slitered; nears slitered; (diode and Schottky and (MOS adj	US-PGPUB;	
		(diode and Schottky and (nos des) transistor) and (silicon near5 substrate)	EPO; JPO;	
			DERWENT	
		large silicide)) and ((IC (Integrated and)		
	ļ	-::+\\ pearb (Card Module)/	USPAT;	2002/10/21 13:3
	7.		US-PGPUB;	
			EPO; JPO;	
			DERWENT	
		near5 silicide)) and (IC (integrated adj	DERWEIT	
		circuit))		